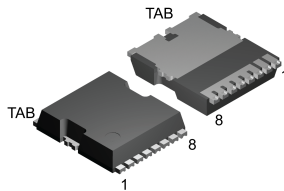
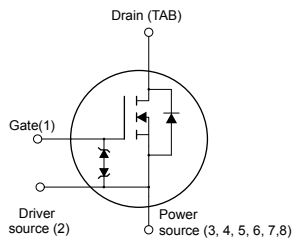


## N-channel 600 V, 48 mΩ typ., 58 A MDmesh DM6 Power MOSFET in a TO-LL package


**TO-LL type A2**


N-chG1DS2PS345678DTABZ



### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$
STO67N60DM6	600 V	59 mΩ	58 A

- Fast-recovery body diode
- Lower  $R_{DS(on)}$  per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

### Applications

- Switching applications

### Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge ( $Q_{rr}$ ), recovery time ( $t_{rr}$ ) and excellent improvement in  $R_{DS(on)}$  per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

#### Product status link

[STO67N60DM6](#)

#### Device summary

<b>Order code</b>	STO67N60DM6
<b>Marking</b>	67N60DM6
<b>Package</b>	TO-LL type A2
<b>Packing</b>	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	58	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	37	
$I_{DM}^{(2)}$	Drain current (pulsed)	190	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	240	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	100	V/ns
$di/dt^{(3)}$	Peak diode recovery current slope	1000	A/ $\mu\text{s}$
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	100	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		$^\circ\text{C}$

1. Referred to TO-247 package.
2. Pulse width is limited by safe operating area.
3.  $I_{SD} \leq 33\text{ A}$ ,  $V_{DS}(\text{peak}) < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$ .
4.  $V_{DS} \leq 480\text{ V}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance, junction-to-case	0.52	$^\circ\text{C/W}$
$R_{thJB}$	Thermal resistance, junction-to-board <sup>(1)</sup>	43	$^\circ\text{C/W}$
	Thermal resistance, junction-to-board <sup>(2)</sup>	22	

1. When mounted on 1 inch<sup>2</sup> FR-4 pcb, standard footprint 2 Oz copper board.
2. When mounted on 40x40mm FR-4 pcb, 6 cm<sup>2</sup> 2 Oz copper board.

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_J$ max.)	9	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	845	mJ

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified.

**Table 4. On /off-states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero-gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}^{(1)}$			100	
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.25	4.00	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 29\text{ A}$		48	59	m $\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	3400	-	pF
$C_{oss}$	Output capacitance		-	280	-	pF
$C_{rSS}$	Reverse transfer capacitance		-	2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ to }480\text{ V}$	-	520	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 52\text{ A}, V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	72.5	-	nC
$Q_{gs}$	Gate-source charge		-	24.5	-	nC
$Q_{gd}$	Gate-drain charge		-	28.5	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 23.75\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 13. Switching times test circuit for resistive load and Figure 18. Switching time waveform)	-	24.5	-	ns
$t_r$	Rise time		-	32	-	ns
$t_{d(off)}$	Turn-off delay time		-	87.5	-	ns
$t_f$	Fall time		-	8.6	-	ns

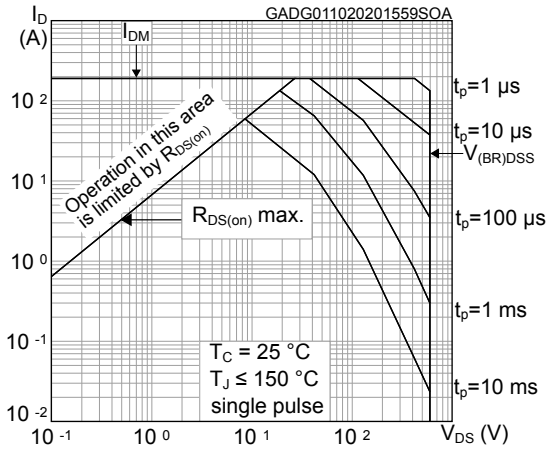
**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		58	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		190	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 58\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 47.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	125		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	0.6		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	9.6		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 47.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	228		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	-	2.34		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	20.5		A

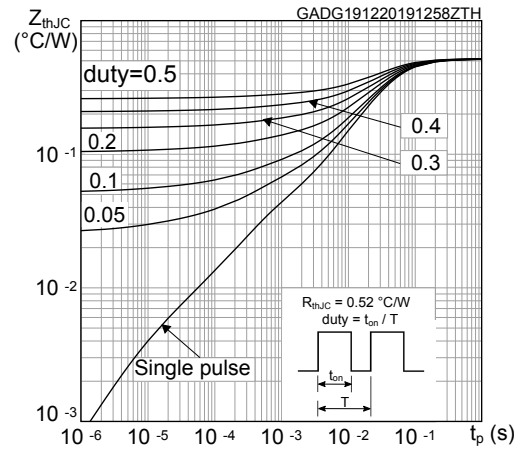
1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

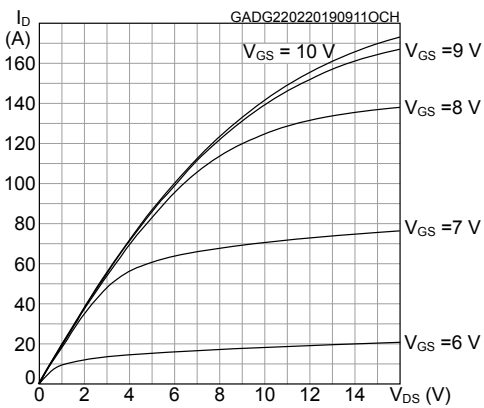
**Figure 1. Safe operating area**



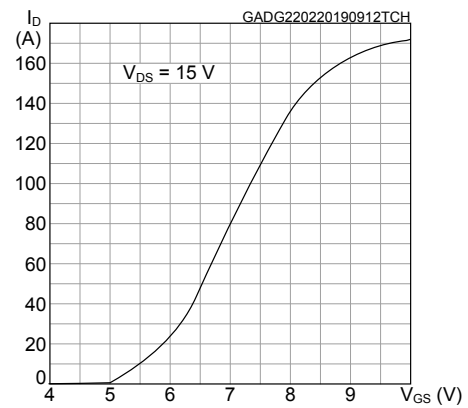
**Figure 2. Maximum transient thermal impedance**



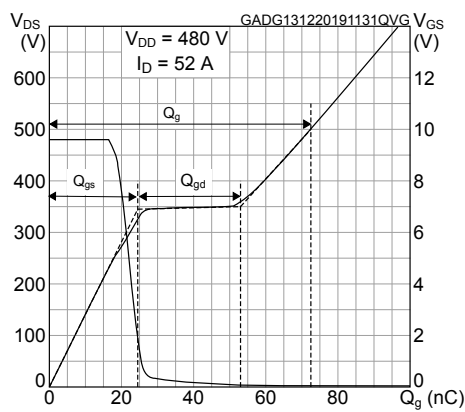
**Figure 3. Typical output characteristics**



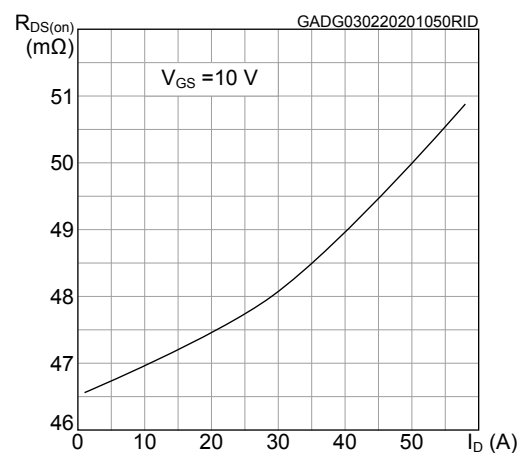
**Figure 4. Typical transfer characteristics**



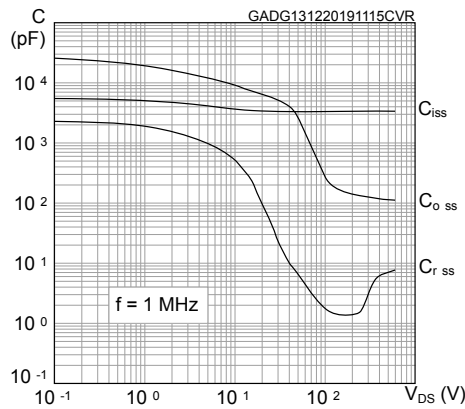
**Figure 5. Typical gate charge characteristics**



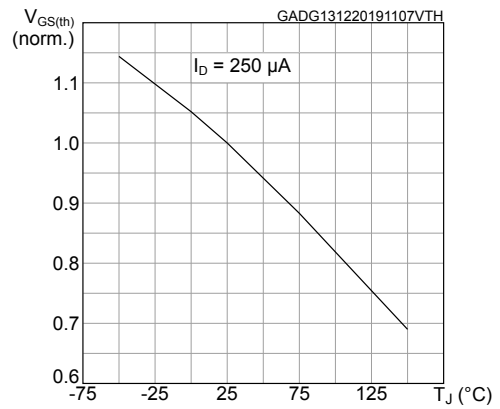
**Figure 6. Typical drain-source on-resistance**



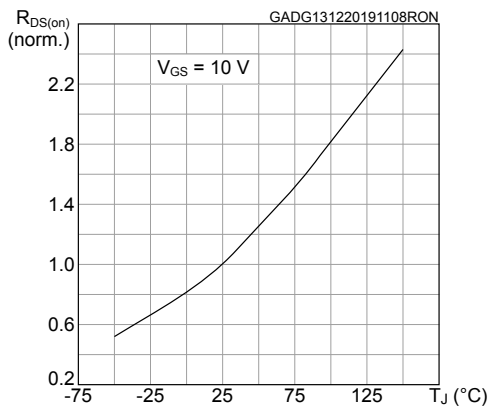
**Figure 7. Typical capacitance characteristics**



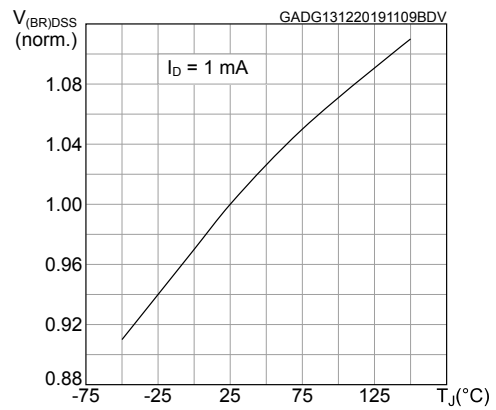
**Figure 8. Normalized gate threshold vs. temperature**



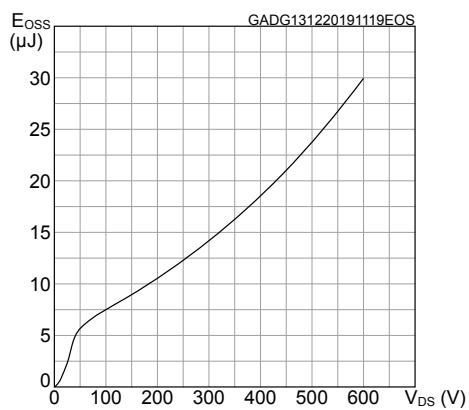
**Figure 9. Normalized on-resistance vs. temperature**



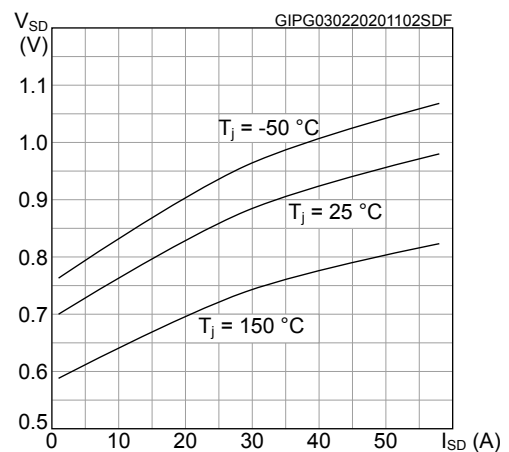
**Figure 10. Normalized breakdown voltage vs temperature**



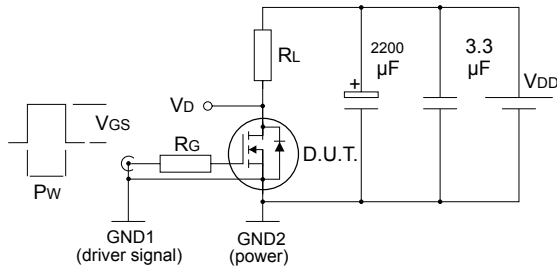
**Figure 11. Output capacitance stored energy**



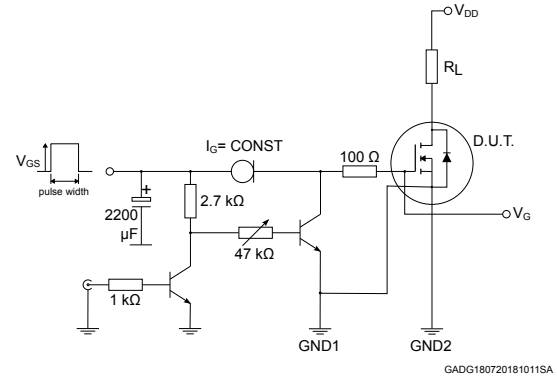
**Figure 12. Typical reverse diode forward characteristics**



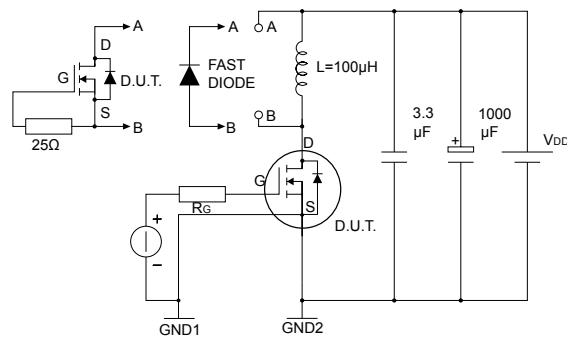
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**


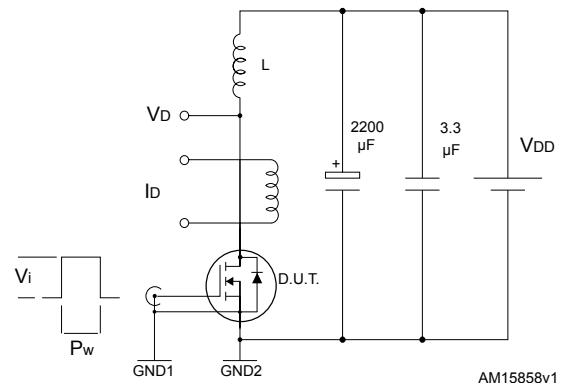
AM15855v1

**Figure 14. Test circuit for gate charge behavior**


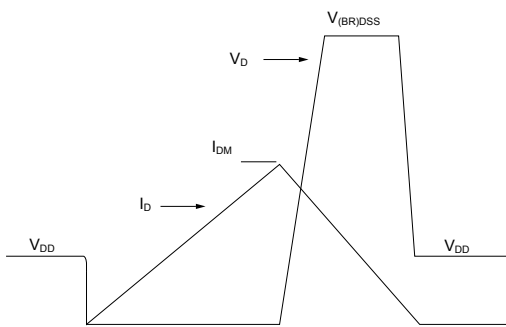
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**Figure 15. Test circuit for inductive load switching and diode recovery times**


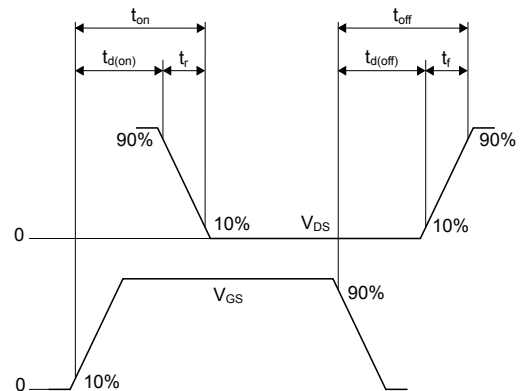
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**Figure 16. Unclamped inductive load test circuit**


AM15858v1

**Figure 17. Unclamped inductive waveform**


AM01472v1

**Figure 18. Switching time waveform**


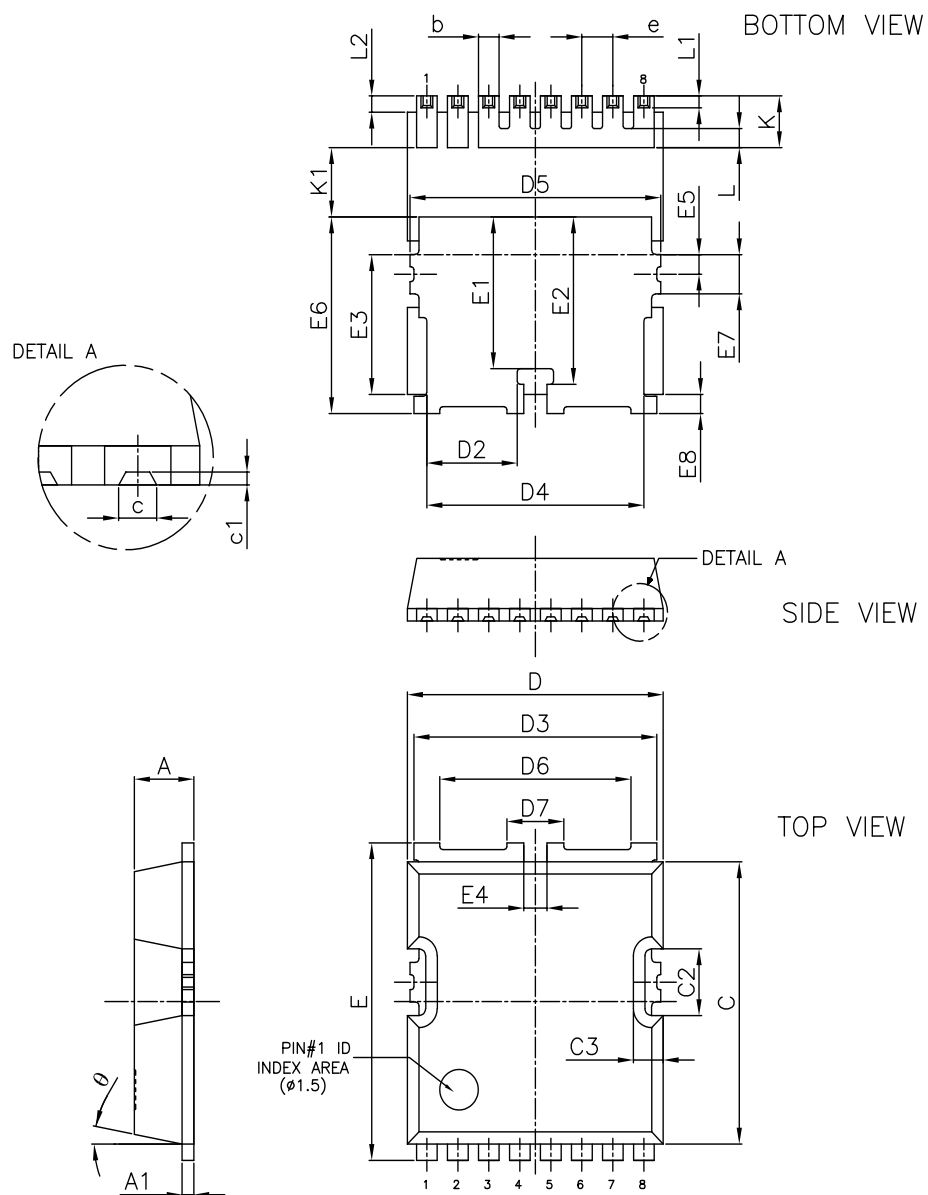
AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-LL type A2 package information

Figure 19. TO-LL type A2 package outline



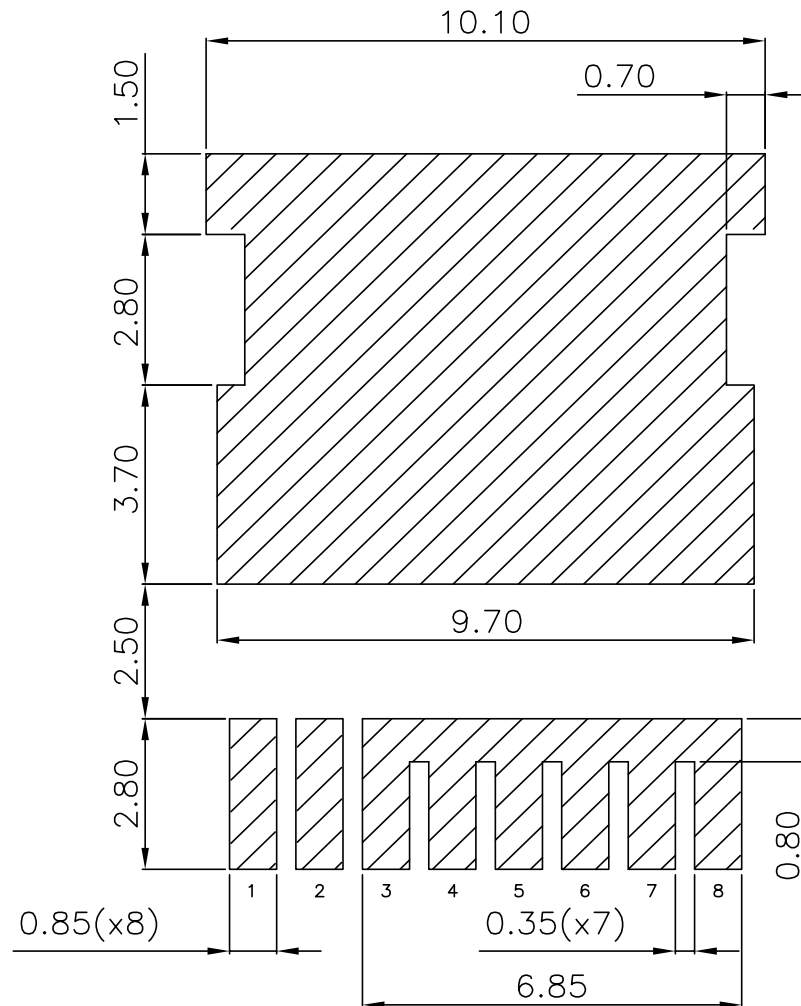
DM00276569\_5\_type\_A2



**Table 8. TO-LL type A2 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.40
A1	0.40	0.48	0.60
b	0.70	0.80	0.90
c		0.46	
c1		0.15	
C	10.28	10.38	10.48
C2	2.35	2.45	2.55
C3		1.16	
D	9.80	9.90	10.00
D2	3.30	3.50	3.70
D3	9.30	9.40	9.50
D4	8.20	8.40	8.60
D5	9.50	9.70	9.90
D6		7.40	
D7		2.20	
e		1.20	
E	11.48	11.68	11.88
E1		5.58	
E2		6.15	
E3		5.14	
E4		0.90	
E5		0.72	
E6	7.03	7.23	7.43
E7		1.44	
E8	0.50	0.70	0.90
K	1.70	1.90	2.10
K1	2.40		
L		0.70	
L1		0.44	
L2	0.40	0.60	0.80
θ		11°	

Figure 20. TO-LL type A2 recommended footprint (dimensions are in mm)



DM00276569\_5\_type\_A2

## 4.2 TO-LL packing information

Figure 21. Carrier tape outline and dimensions

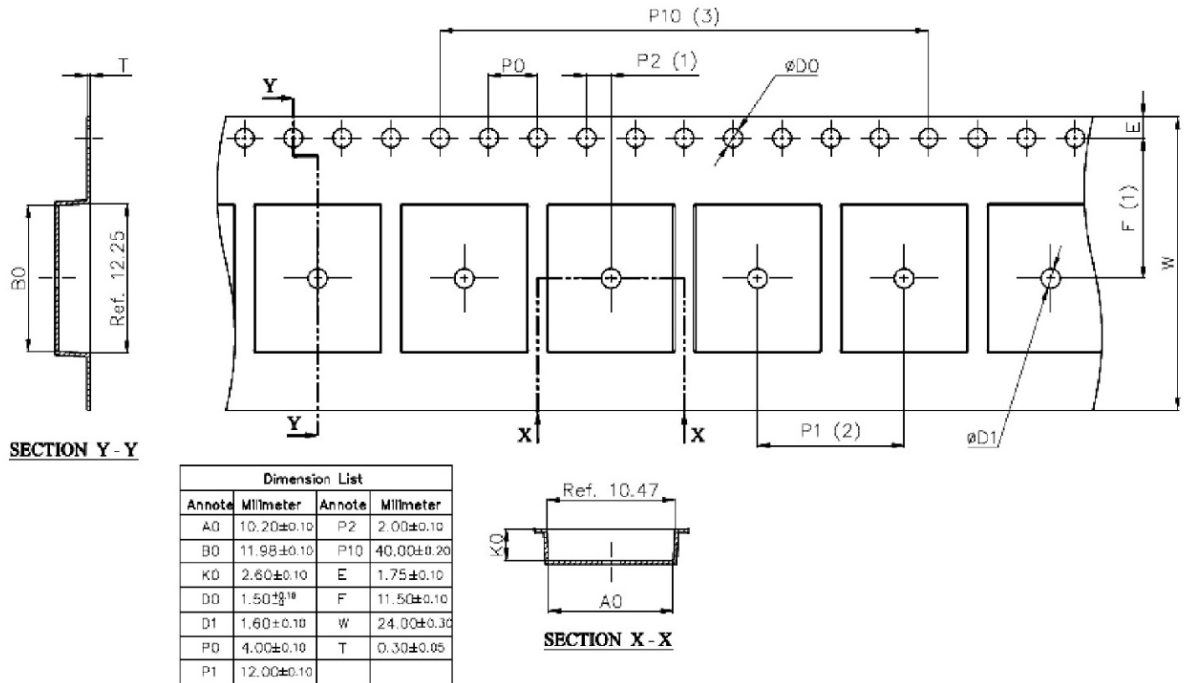
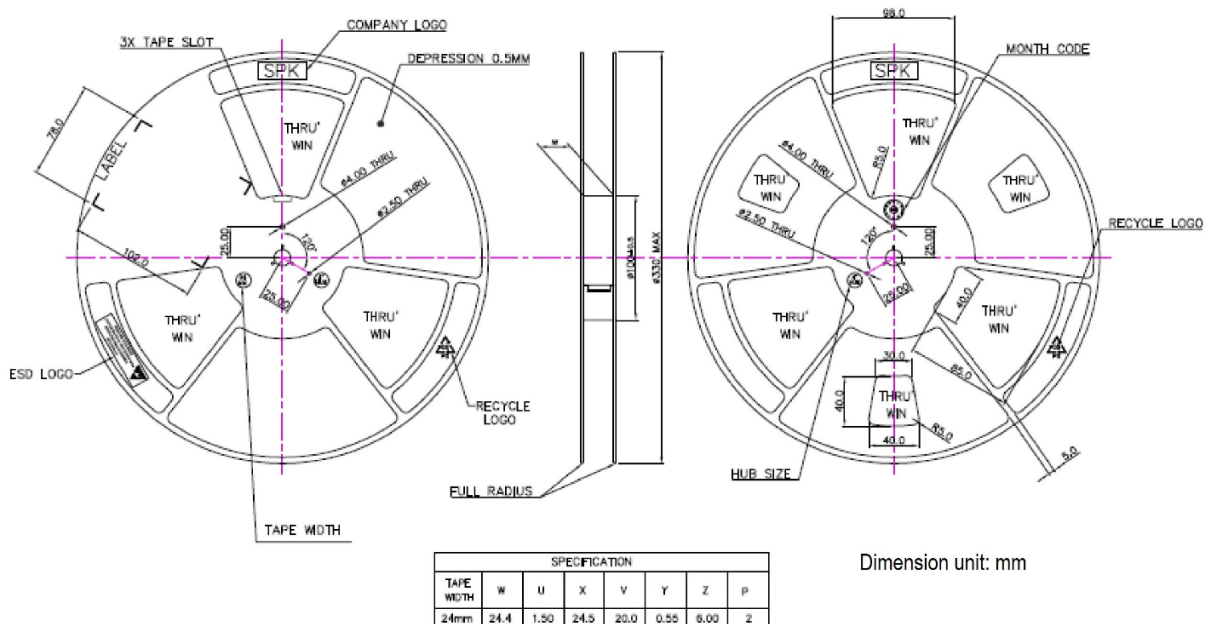
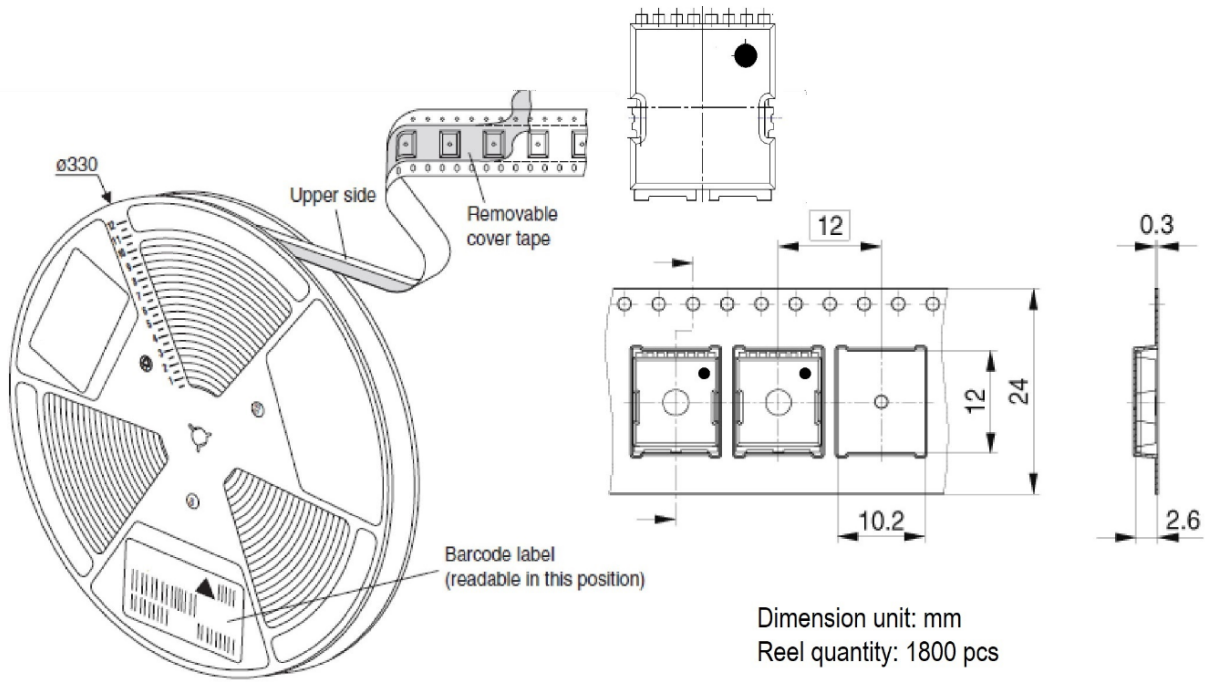


Figure 22. Reel outline and dimensions



**Figure 23. TO-LL orientation in tape pocket**



## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
03-Feb-2020	1	First release.
20-Mar-2020	2	Updated title of the document, section <i>Features</i> , <i>Table 1. Absolute maximum ratings</i> , <i>Table 4. On /off-states</i> and <i>Table 7. Source-drain diode</i> .
28-Jul-2020	3	Updated <i>Table 1. Absolute maximum ratings</i> . Added <i>Section 4.2 TO-LL packing information</i> .
30-Apr-2021	4	Updated <i>title</i> and <i>Device summary</i> in cover page. Updated <i>Section 4 Package information</i> . Minor text changes.
08-Jun-2021	5	Modified features and $I_D$ value on cover page. Modified <i>Table 1. Absolute maximum ratings</i> , <i>Table 2. Thermal data</i> , <i>Table 4. On /off-states</i> and <i>Table 7. Source-drain diode</i> . Modified <i>Figure 1. Safe operating area</i> , <i>Figure 2. Maximum transient thermal impedance</i> , <i>Figure 6. Typical drain-source on-resistance</i> and <i>Figure 12. Typical reverse diode forward characteristics</i> . Minor text changes.

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